Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = +25°C
20V	0.55Ω @ V_{GS} = 4.5V	630mA
	0.9Ω @ V_{GS} = 1.8V	410mA

Features and Benefits

- Low On-Resistance: $R_{DS(on)}$ = $550_{(max)}$mΩ @ V_{GS} = 4.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected up to 2KV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

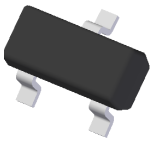
- DC-DC Converters
- Power Management Functions

Mechanical Data

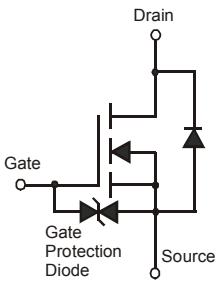
- Case: SOT23 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



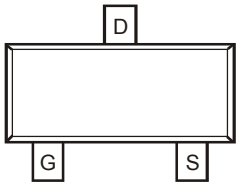
SOT23



Top View



Equivalent Circuit



Top View

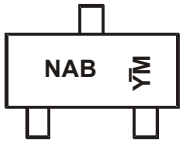
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2004K-7	SOT23 (Standard)	3000/Tape & Reel

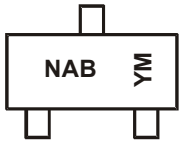
Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information



Chengdu A/T Site



Shanghai A/T Site

NAB = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}$M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: I = 2021)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	……	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V	……	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +85°C	I_D	630 450	mA
Drain Current (Note 5) V_{GS} = 1.8V	Steady State	T_A = +25°C T_A = +85°C	I_D	410 300	mA
Pulsed Drain Current (Note 6)			I_{DM}	1.5	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

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Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1	μA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	0.4 0.5 0.7	0.55 0.70 0.9	Ω	V_{GS} = 4.5V, I_D = 540mA V_{GS} = 2.5V, I_D = 500mA V_{GS} = 1.8V, I_D = 350mA
Forward Transfer Admittance	$\|Y_{fs}\|$	200	—	—	ms	V_{DS} =10V, I_D = 0.2A
Source Current	I_S	—	—	0.5	A	—
Diode Forward Voltage (Note 7)	V_{SD}	0.6	—	1	V	V_{GS} = 0V, I_S = 500mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	150	pF	V_{DS} = 16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	20	pF	
Gate Resistance	R_g	—	292	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	0.9	—	nC	V_{DS} = 15V, V_{GS} = 4.5V, I_D = 0.5A
Gate-Source Charge	Q_{gs}	—	0.2	—		
Gate-Drain Charge	Q_{gd}	—	0.2	—		
Turn-On Delay Time	$t_{D(on)}$	—	5.7	—	ns	V_{GS} = 8V, V_{DS} = 15V, R_G = 6Ω, R_L = 30Ω
Turn-On Rise Time	t_r	—	8.4	—		
Turn-Off Delay Time	$t_{D(off)}$	—	59.4	—		
Turn-Off Fall Time	t_f	—	37.6	—		
Body Diode Reverse Recovery Time	t_{rr}	—	5.5	—	ns	I_S = 0.5A, dI/dt = -100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	—	0.85	—	nC	I_S = 0.5A, dI/dt = -100A/μs

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
6. Pulse width ≤10μS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.

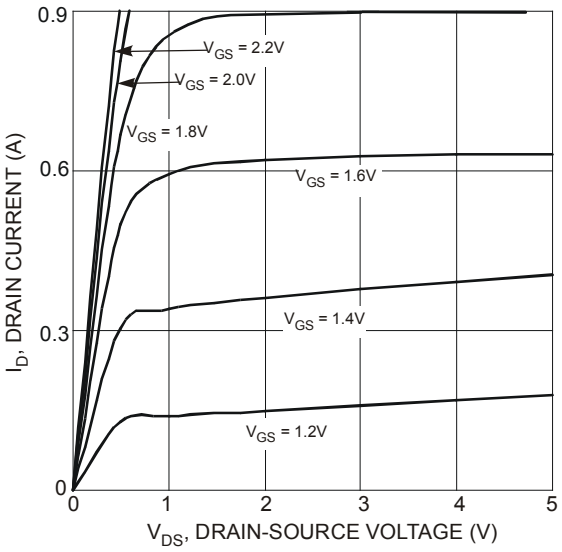


Figure 1 Typical Output Characteristics

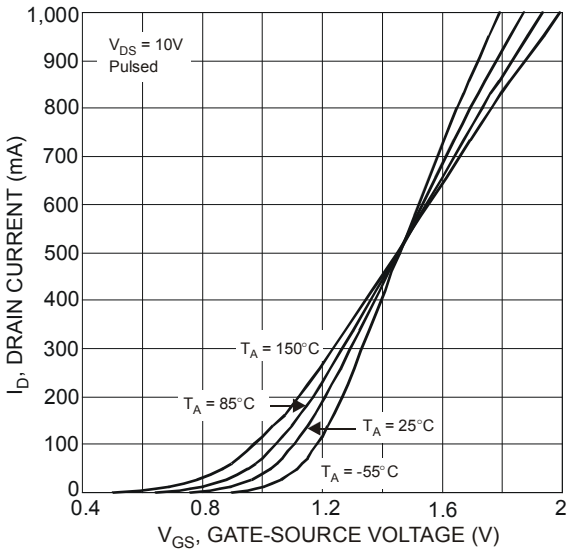


Figure 2 Reverse Drain Current vs. Source-Drain Voltage

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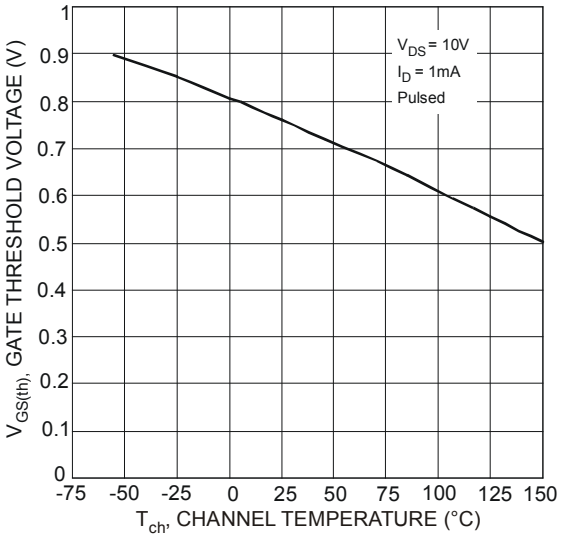


Figure 3 Gate Threshold Voltage vs. Channel Temperature

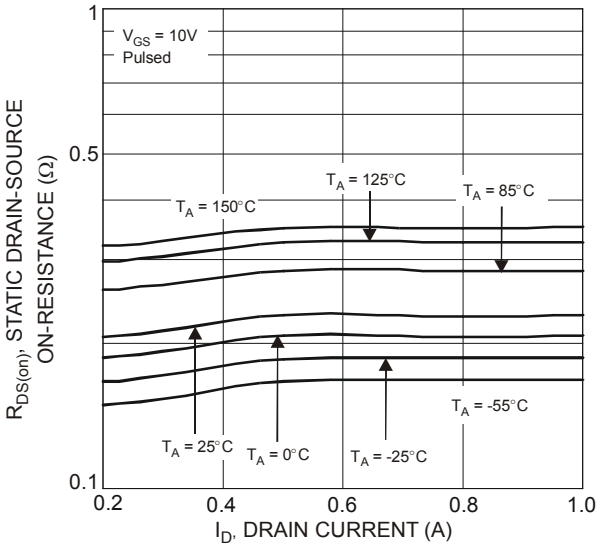


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

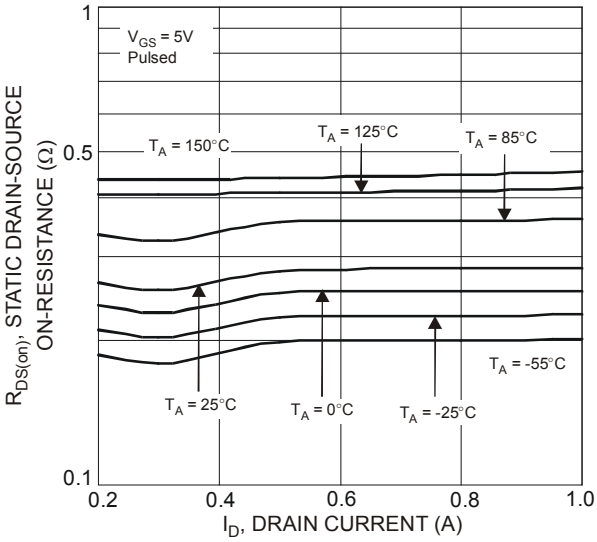


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

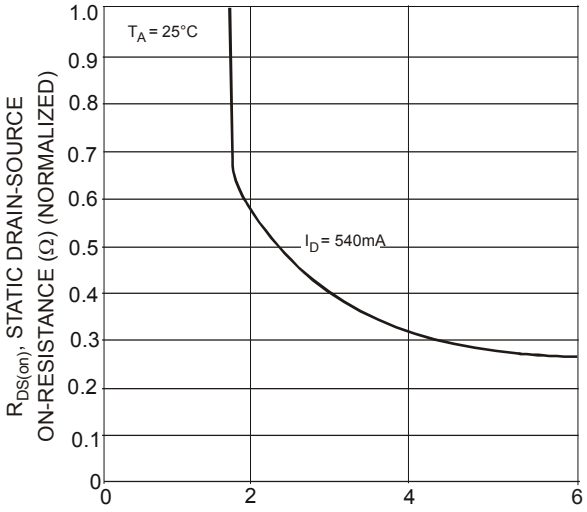


Figure 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

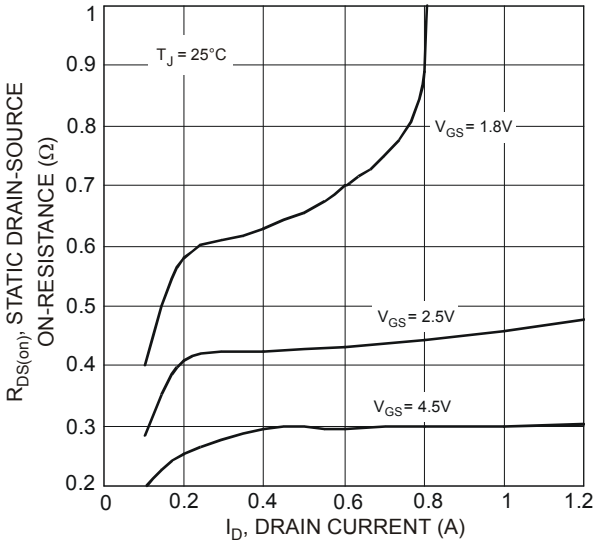


Figure 7 On-Resistance vs. Drain Current and Gate Voltage

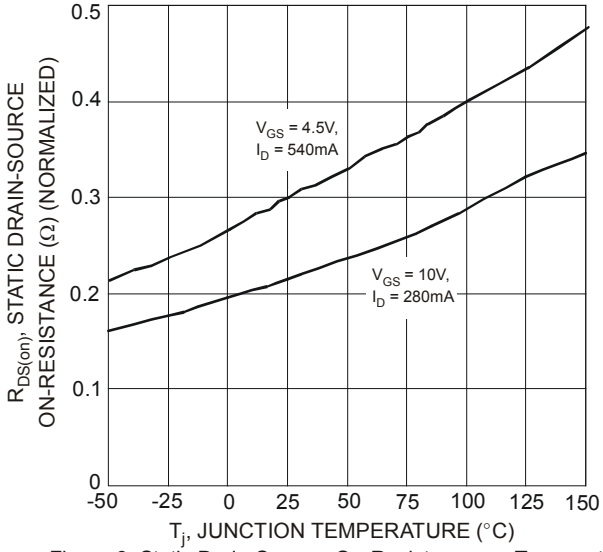


Figure 8 Static Drain-Source, On-Resistance vs. Temperature

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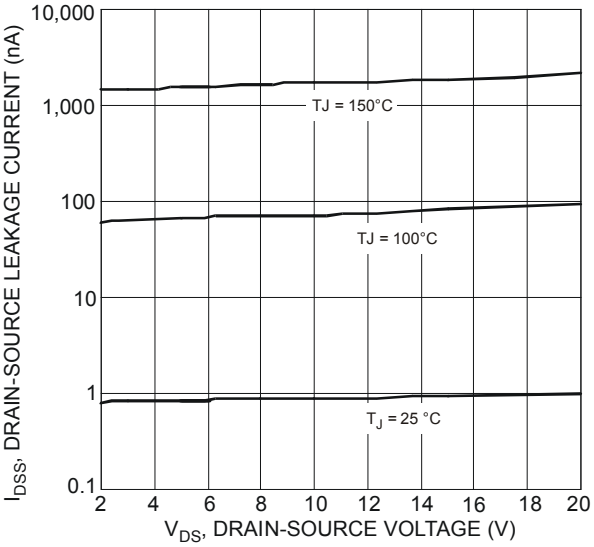


Figure 9 Drain Source Leakage Current vs. Voltage

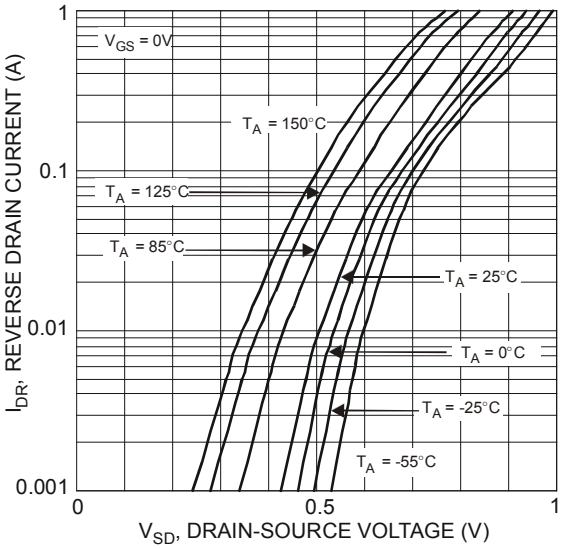


Figure 10 Reverse Drain Current vs. Source-Drain Voltage

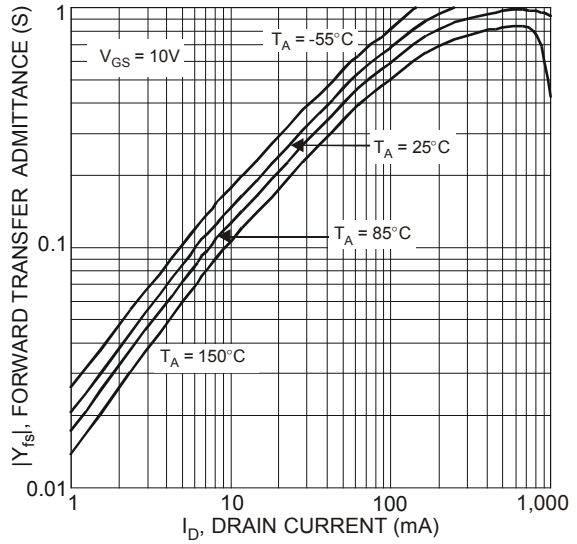


Figure 11 Forward Transfer Admittance vs. Drain Current

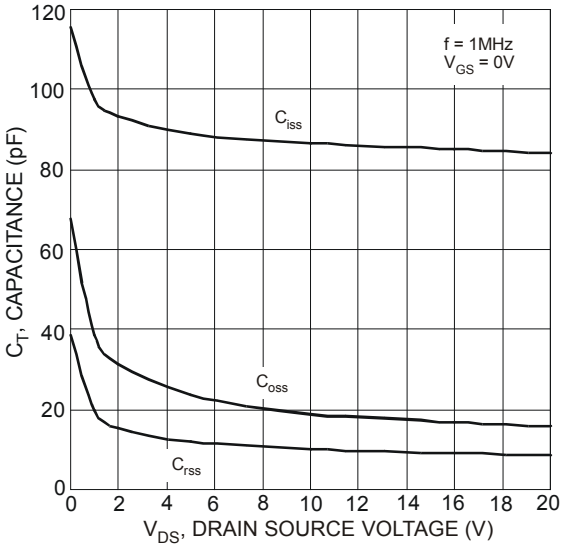


Figure 12 Capacitance Variation

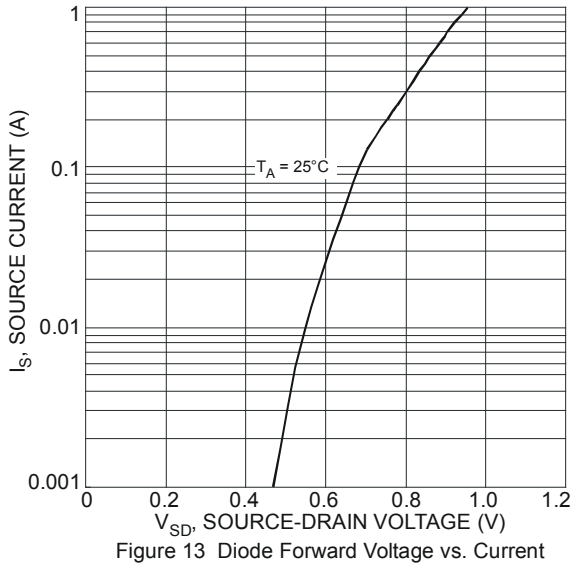


Figure 13 Diode Forward Voltage vs. Current

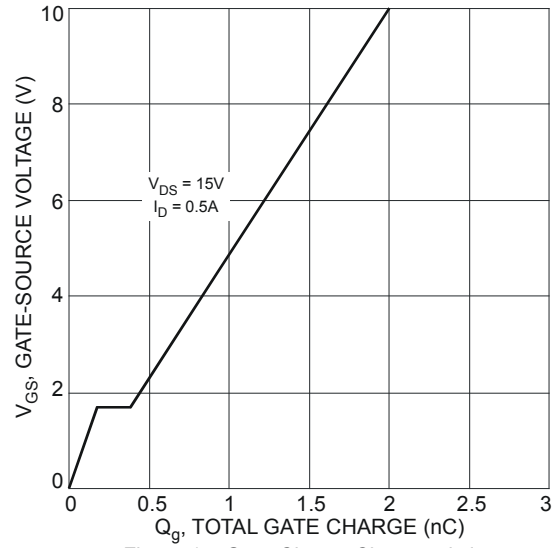


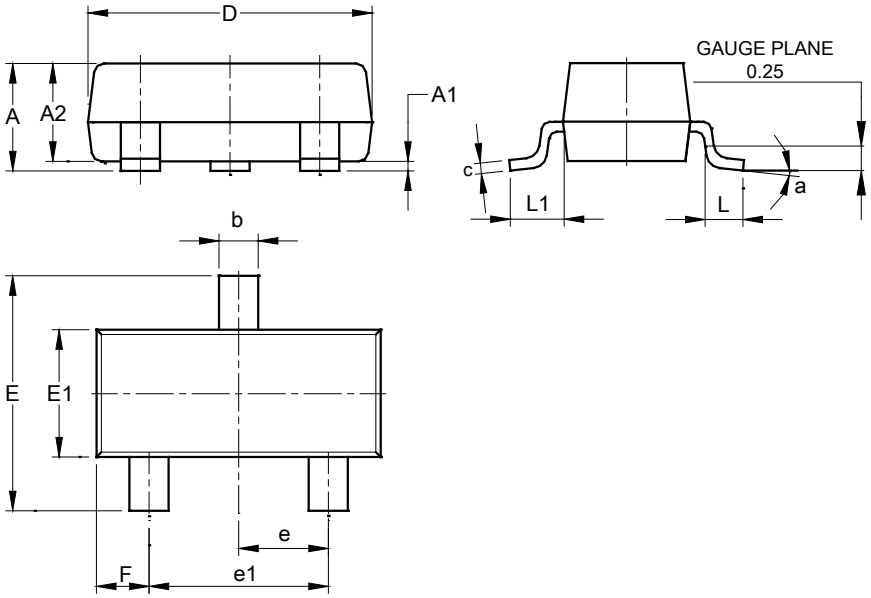
Figure 14 Gate-Charge Characteristics

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)

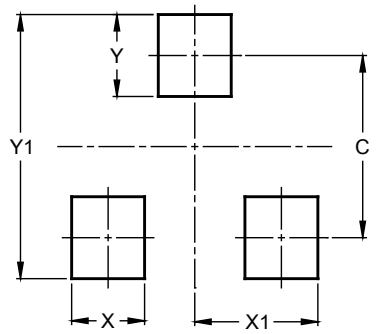


SOT23 (Standard)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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